

CSE 490/590 Computer Architecture

Cache I

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Last Time...

- Pipelining hazards
 - Structural hazards
 - Data hazards
 - Control hazards
- Data hazards
 - Stall
 - Bypass
- Control hazards
 - Jump
 - Conditional branch

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Branch Delay Slots (expose control hazard to software)

- Change the ISA semantics so that the instruction that follows a jump or branch is always executed
 - gives compiler the flexibility to put in a useful instruction where normally a pipeline bubble would have resulted.

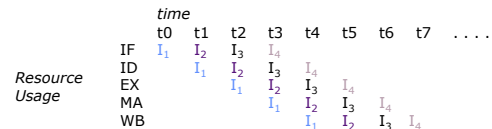
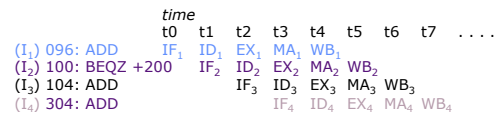
I ₁	096	ADD	
I ₂	100	BEQZ r1 +200	Delay slot instruction
I ₃	104	ADD	executed regardless of
I ₄	304	ADD	branch outcome

- Other techniques include more advanced branch prediction, which can dramatically reduce the branch penalty... to come later

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Branch Pipeline Diagrams (branch delay slot)



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Why an Instruction may not be dispatched every cycle (CPI>1)

- Full bypassing may be too expensive to implement
 - typically all frequently used paths are provided
 - some infrequently used bypass paths may increase cycle time and counteract the benefit of reducing CPI
- Loads have two-cycle latency
 - Instruction after load cannot use load result
 - MIPS-I ISA defined *load delay slots*, a software-visible pipeline hazard (compiler schedules independent instruction or inserts NOP to avoid hazard). Removed in MIPS-II (pipeline interlocks added in hardware)
 - » MIPS: "Microprocessor without Interlocked Pipeline Stages"
- Conditional branches may cause bubbles
 - Kill following instruction(s) if no delay slots

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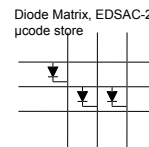
Early Read-Only Memory Technologies



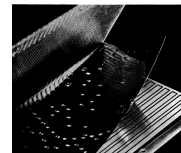
Punched cards. From early 1700s through Jaquard Loom, Babbage, and then IBM



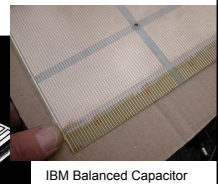
Punched paper tape, instruction stream in Harvard Mk 1



Diode Matrix, EDSAC-2 µcode store



IBM Card Capacitor ROS



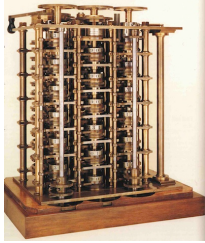
IBM Balanced Capacitor ROS

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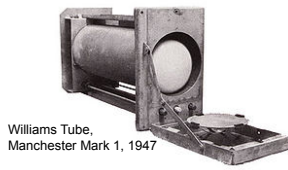
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Early Read/Write Main Memory Technologies

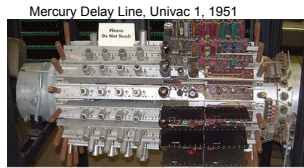
Babbage, 1800s: Digits stored on mechanical wheels



Also, regenerative capacitor memory on Atanasoff-Berry computer, and rotating magnetic drum memory on IBM 650



Williams Tube, Manchester Mark 1, 1947



Mercury Delay Line, Univac 1, 1951

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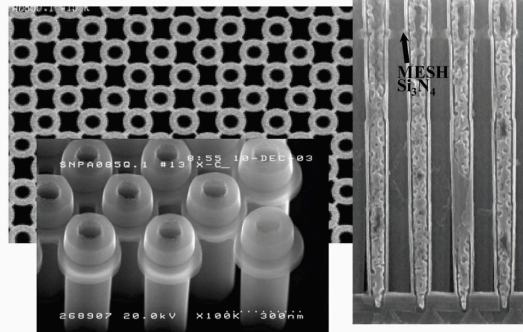
Semiconductor Memory

- Semiconductor memory began to be competitive in early 1970s
 - Intel formed to exploit market for semiconductor memory
 - Early semiconductor memory was Static RAM (SRAM). SRAM cell internals similar to a latch (cross-coupled inverters).
- First commercial Dynamic RAM (DRAM) was Intel 1103
 - 1Kbit of storage on single chip
 - charge on a capacitor used to hold value
- Semiconductor memory quickly replaced core in '70s

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Modern DRAM Structure

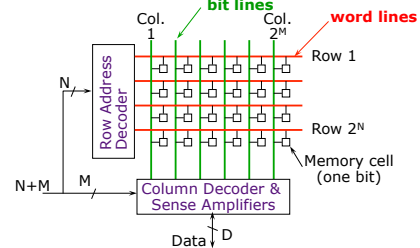


[Samsung, sub-70nm DRAM, 2004]

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DRAM Architecture



- Bits stored in 2-dimensional arrays on chip
- Modern chips have around 4 logical banks on each chip
 - each logical bank physically implemented as many smaller arrays

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DRAM Operation

Three steps in read/write access to a given bank

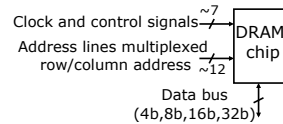
- Row access (RAS)
 - decode row address, enable addressed row (often multiple Kb in row)
 - bitlines share charge with storage cell
 - small change in voltage detected by sense amplifiers which latch whole row of bits
 - sense amplifiers drive bitlines full rail to recharge storage cells
- Column access (CAS)
 - decode column address to select small number of sense amplifier latches (4, 8, 16, or 32 bits depending on DRAM package)
 - on read, send latched bits out to chip pins
 - on write, change sense amplifier latches which then charge storage cells to required value
 - can perform multiple column accesses on same row without another row access (burst mode)
- Precharge
 - charges bit lines to known value, required before next row access

Each step has a latency of around 15-20ns in modern DRAMs
Various DRAM standards (DDR, RDRAM) have different ways of encoding the signals for transmission to the DRAM, but all share same core architecture

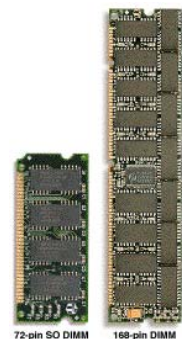
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DRAM Packaging



- DIMM (Dual Inline Memory Module) contains multiple chips with clock/control/address signals connected in parallel (sometimes need buffers to drive signals to all chips)
- Data pins work together to return wide word (e.g., 64-bit data bus using 16x4-bit parts)

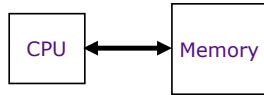


72-pin SO DIMM 168-pin DIMM

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CPU-Memory Bottleneck



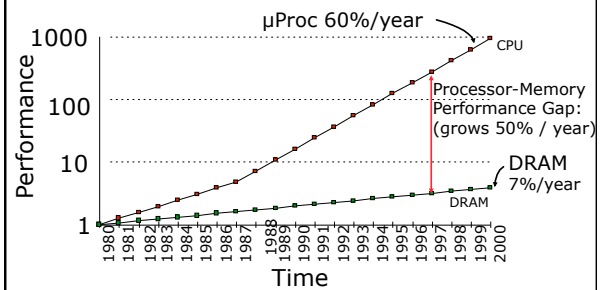
Performance of high-speed computers is usually limited by memory *bandwidth* & *latency*

- **Latency** (time for a single access)
Memory access time \gg Processor cycle time
Problematic
- **Bandwidth** (number of accesses per unit time)
Increase the bus size, etc.
Usually OK

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Processor-DRAM Gap (latency)

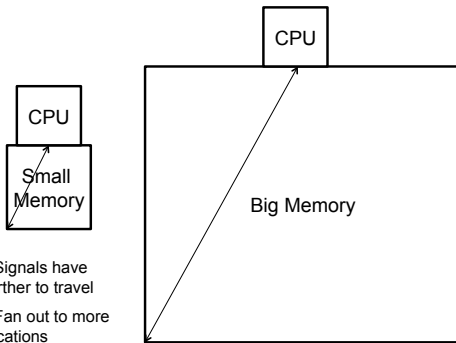


Four-issue 2GHz superscalar accessing 100ns DRAM could execute 800 instructions during time for one memory access!

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Physical Size Affects Latency



- Signals have further to travel
- Fan out to more locations

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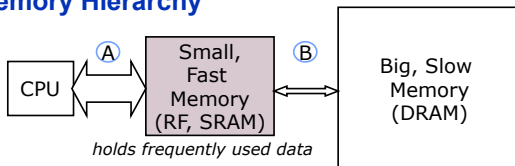
CSE 490/590 Administrivia

- Very important to attend
 - Recitations next week & the week after
- Guest lectures
 - There will be a couple guest lectures late Feb/early Mar.
- Quiz 1
 - Rescheduled
 - Fri, 2/11
 - Closed book, in-class
 - Includes lectures until last Monday (1/31)
 - Review: next Wed (2/9)

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Memory Hierarchy



- **capacity:** Register \ll SRAM \ll DRAM *why?*
- **latency:** Register \ll SRAM \ll DRAM *why?*
- **bandwidth:** on-chip \gg off-chip *why?*

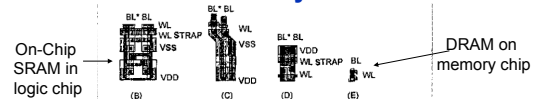
On a data access:

- if data \in fast memory \Rightarrow low latency access (SRAM)*
- If data \notin fast memory \Rightarrow long latency access (DRAM)*

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Relative Memory Cell Sizes



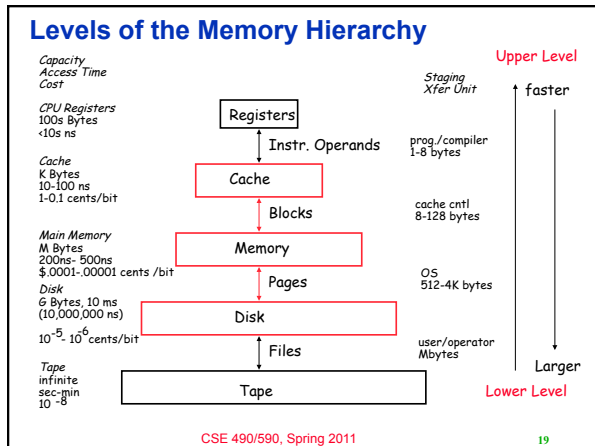
1 Memory cell in 0.5 μ m processes

- Gate Array SRAM
- Embedded SRAM
- Standard SRAM (6T cell with local interconnect)
- ASIC DRAM
- Standard DRAM (stacked cell)

[Foss, "Implementing Application-Specific Memory", ISSCC 1996]

Memory	Process	Cell size (μm^2)	Cell efficiency	Hits in $100\text{mm}^2 (10^4)$	Gate size (μm^2)	Gate utilization	Gates in $100\text{mm}^2 (10^4)$
Gate array SRAM	3-metal ASIC	370	80%	216	185	70%	378
Embedded SRAM	3-metal ASIC	67	70%	1045	185	70%	378
Standard SRAM	2-metal 6T local int.	43	69%	1512	245	40%	165
Embedded ASIC-DRAM	3-metal ASIC	23	60%	2609	185	70%	378
Standard DRAM	2-metal stacked cell	3.2	50%	15625	411	40%	97

Table 1: Memory and logic density for a variety of 0.5 μ m implementations.



Memory Hierarchy: Apple iMac G5

	Reg	L1 Inst	L1 Data	L2	DRAM	Disk
Size	1K	64K	32K	512K	256M	80G
Latency Cycles, Time	1, 0.6 ns	3, 1.9 ns	3, 1.9 ns	11, 6.9 ns	88, 55 ns	10 ⁷ , 12 ms

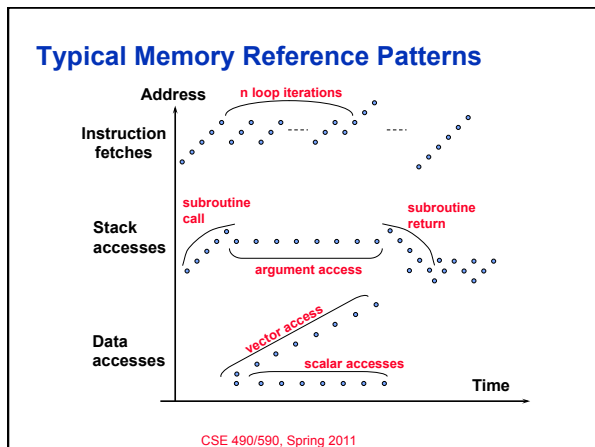
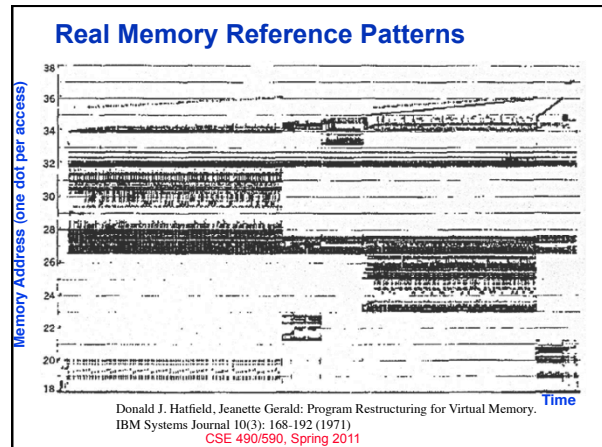
Goal: Illusion of large, fast, cheap memory

Let programs address a memory space that scales to the disk size, at a speed that is usually as fast as register access

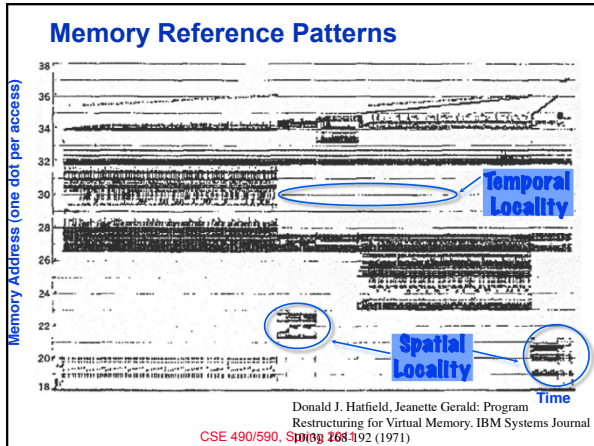
iMac G5 1.6 GHz

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- ### Management of Memory Hierarchy
- Small/fast storage, e.g., registers
 - Address usually specified in instruction
 - Generally implemented directly as a register file
 - » but hardware might do things behind software's back, e.g., stack management, register renaming
 - Larger/slower storage, e.g., main memory
 - Address usually computed from values in register
 - Generally implemented as a hardware-managed cache hierarchy
 - » hardware decides what is kept in fast memory
 - » but software may provide "hints", e.g., don't cache or prefetch
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- ### Common Predictable Patterns
- Two predictable properties of memory references:
- **Temporal Locality:** If a location is referenced it is likely to be referenced again in the near future.
 - **Spatial Locality:** If a location is referenced it is likely that locations near it will be referenced in the near future.
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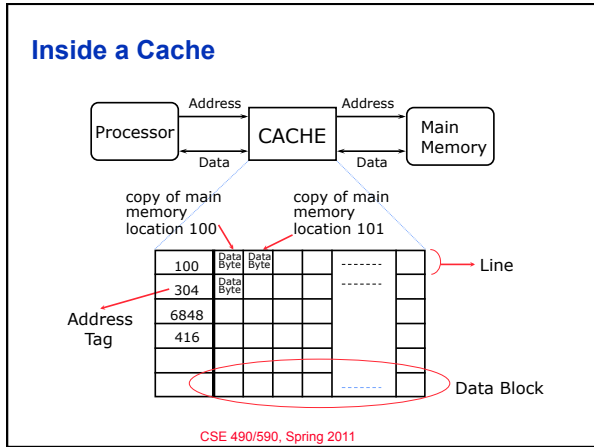


Caches

Caches exploit both types of predictability:

- Exploit temporal locality by remembering the contents of recently accessed locations.
- Exploit spatial locality by fetching blocks of data around recently accessed locations.

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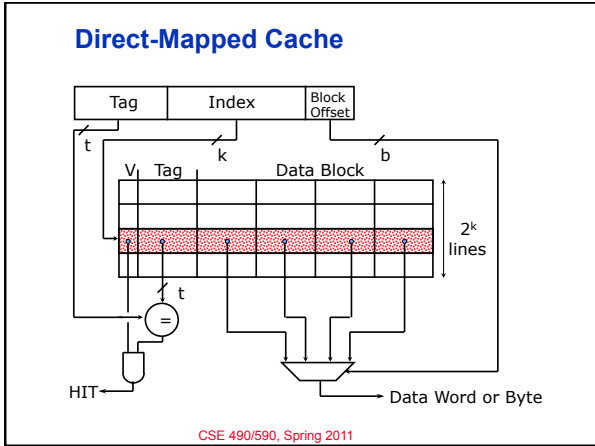
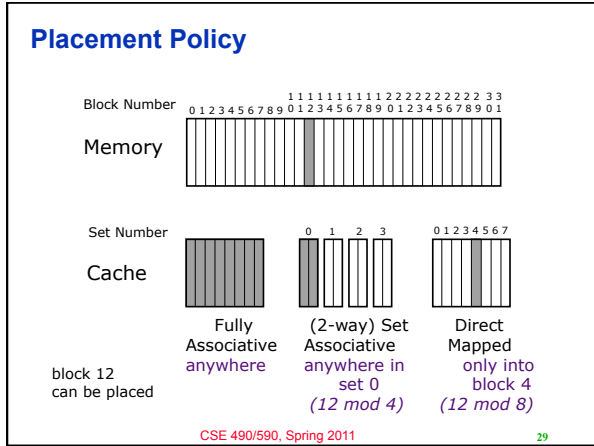


Cache Algorithm (Read)

Look at Processor Address, search cache tags to find match. Then either

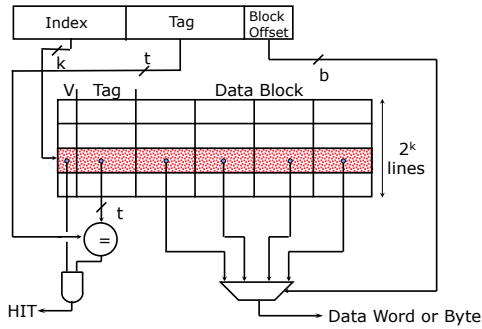
- Found in cache a.k.a. HIT
 - Return copy of data from cache
- Not in cache a.k.a. MISS
 - Read block of data from Main Memory
 - Wait ...
 - Return data to processor and update cache
 - Q: Which line do we replace?

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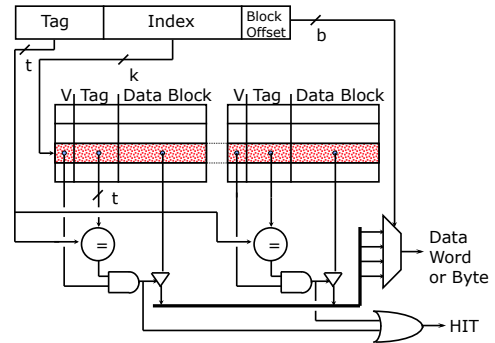
Direct Map Address Selection

higher-order vs. lower-order address bits



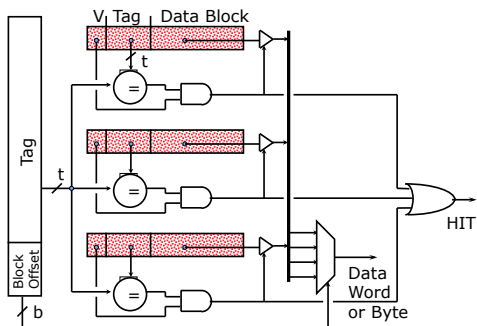
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2-Way Set-Associative Cache



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Fully Associative Cache



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Replacement Policy

In an associative cache, which block from a set should be evicted when the set becomes full?

- Random
- Least Recently Used (LRU)
 - LRU cache state must be updated on every access
 - true implementation only feasible for small sets (2-way)
 - pseudo-LRU binary tree often used for 4-8 way
- First In, First Out (FIFO) a.k.a. Round-Robin
 - used in highly associative caches
- Not Least Recently Used (NLRU)
 - FIFO with exception for most recently used block or blocks

This is a second-order effect. Why?

Replacement only happens on misses

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Acknowledgements

- These slides heavily contain material developed and copyright by
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